

SI2320DS-T1-E3-VB Datasheet

N-Channel 200 V (D-S) MOSFET

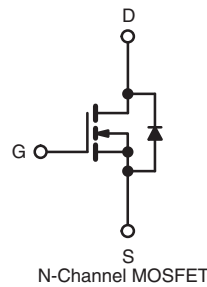
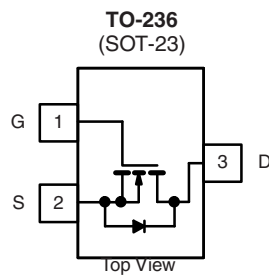
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
200	1.4 at $V_{GS} = 10$ V	0.6

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- 100 % R_g and UIS Tested
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	200		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	0.6	0.45	A
		$T_A = 70$ °C	0.5	0.35	
Pulsed Drain Current ^b	I_{DM}	2.5			
Avalanche Current ^b	I_{AS}	2.5			
Single Avalanche Energy	E_{AS}	50		mJ	
Continuous Source Current (Diode Conduction) ^a	I_S	0.6		A	
Power Dissipation ^a	P_D	$T_A = 25$ °C	1.55	1.03	W
		$T_A = 70$ °C	1.20	0.87	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	R_{thJA}	80	100	°C/W
	Steady State		130	170	
Maximum Junction-to-Foot	Steady State	R_{thJF}	45	55	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

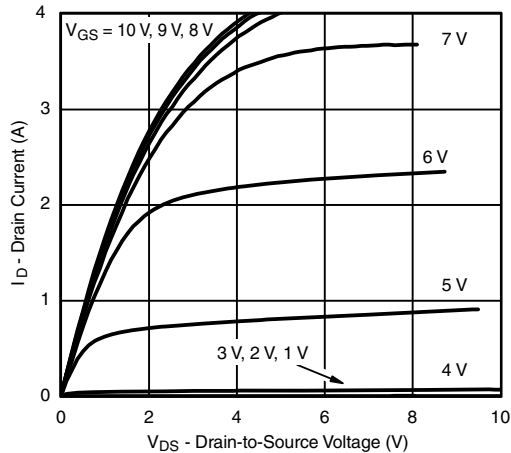
SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 1 mA	200			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5		4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 70 °C			75	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 15 V, V _{GS} = 10 V	2.5			A
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 A		1.4		Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 0.5 A		4		S
Diode Forward Voltage	V _{SD}	I _S = 1 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 100 V, V _{GS} = 10 V, I _D = 0.5 A		3	5	nC
Gate-Source Charge	Q _{gs}			0.37		
Gate-Drain Charge	Q _{gd}			1.45		
Gate Resistance	R _g		0.5	1.3	2.4	Ω
Switching						
Turn-On Delay Time	t _{d(on)}	V _{DD} = 100 V, R _L = 33 Ω I _D ≅ 0.2 A, V _{GEN} = 10 V, R _g = 6 Ω		7	11	ns
Rise Time	t _r			10	15	
Turn-Off Delay Time	t _{d(off)}			9	15	
Fall Time	t _f			11	15	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.5 A, di/dt = 100 A/μs50100				

Notes:

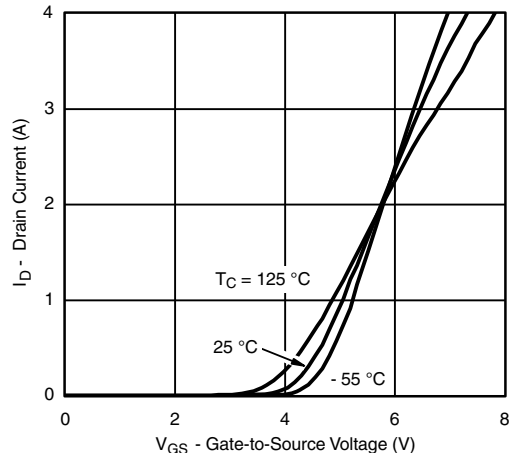
- a. Pulse test: PW ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

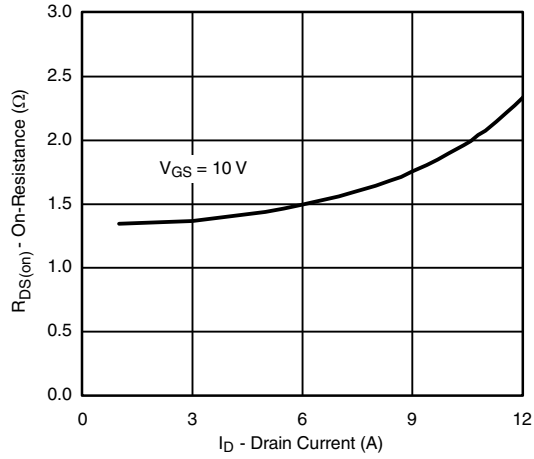


Output Characteristics

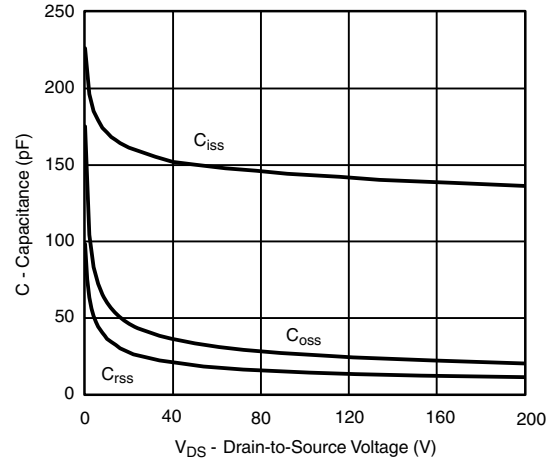


Transfer Characteristics

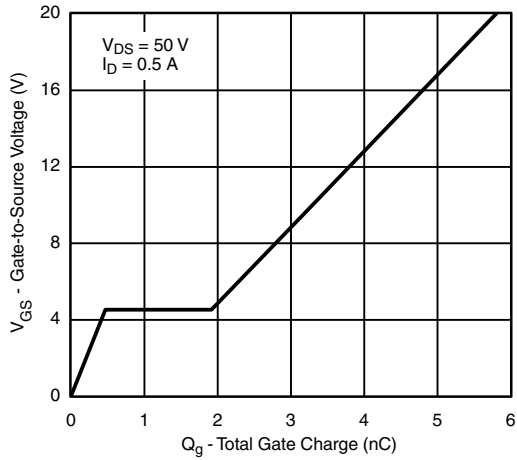
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



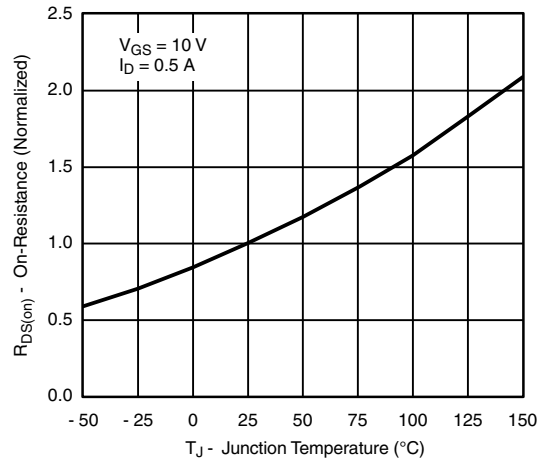
On-Resistance vs. Drain Current



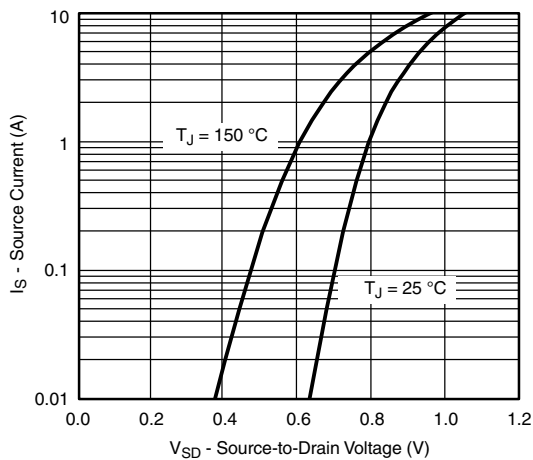
Capacitance



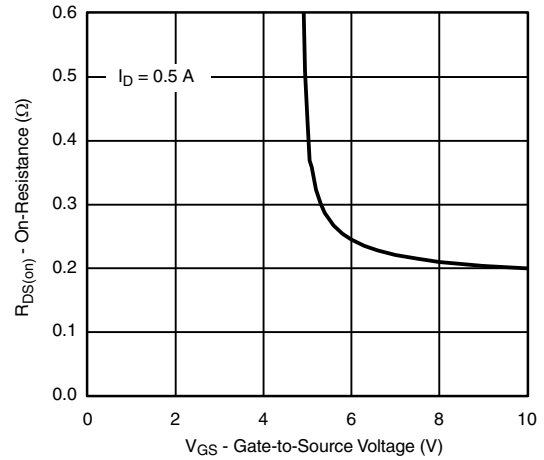
Gate Charge



On-Resistance vs. Junction Temperature

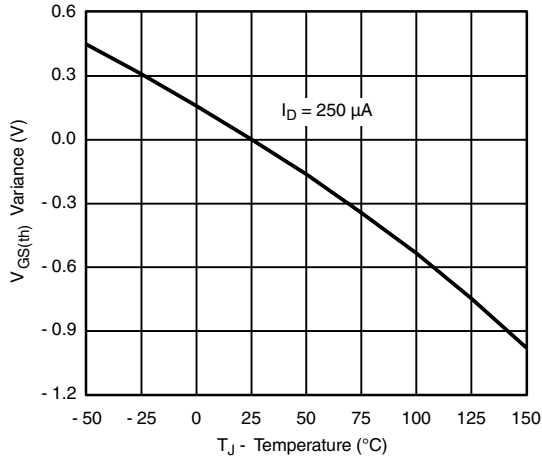


Source-Drain Diode Forward Voltage

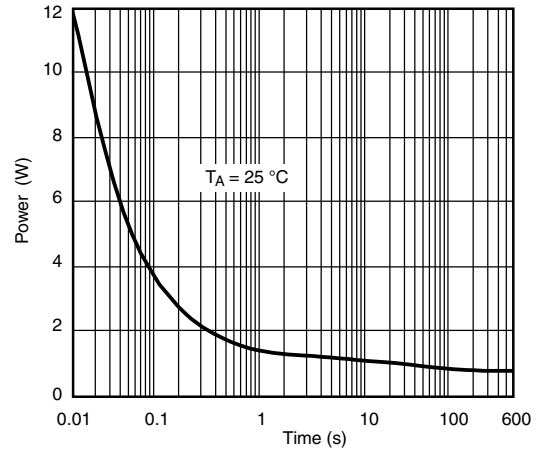


On-Resistance vs. Gate-to-Source Voltage

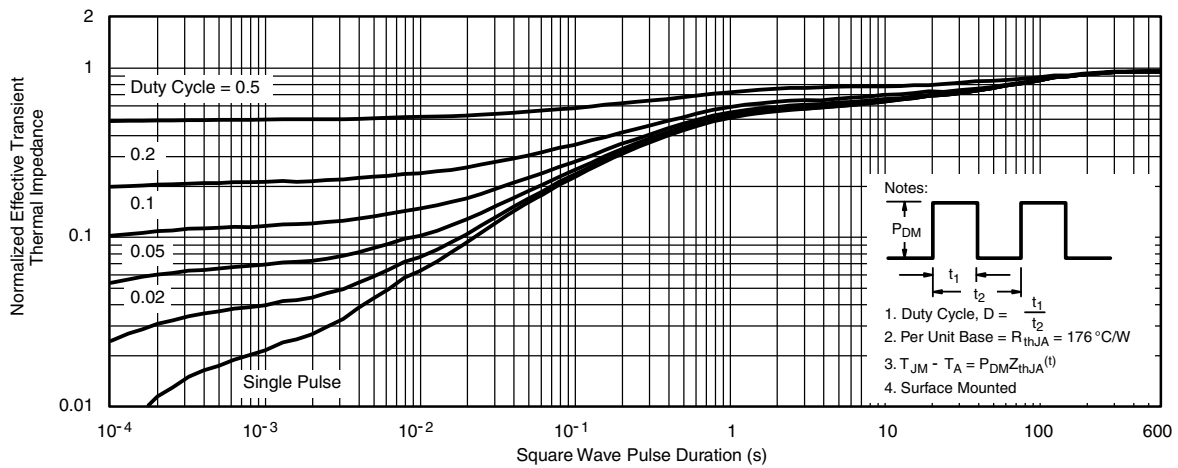
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Threshold Voltage

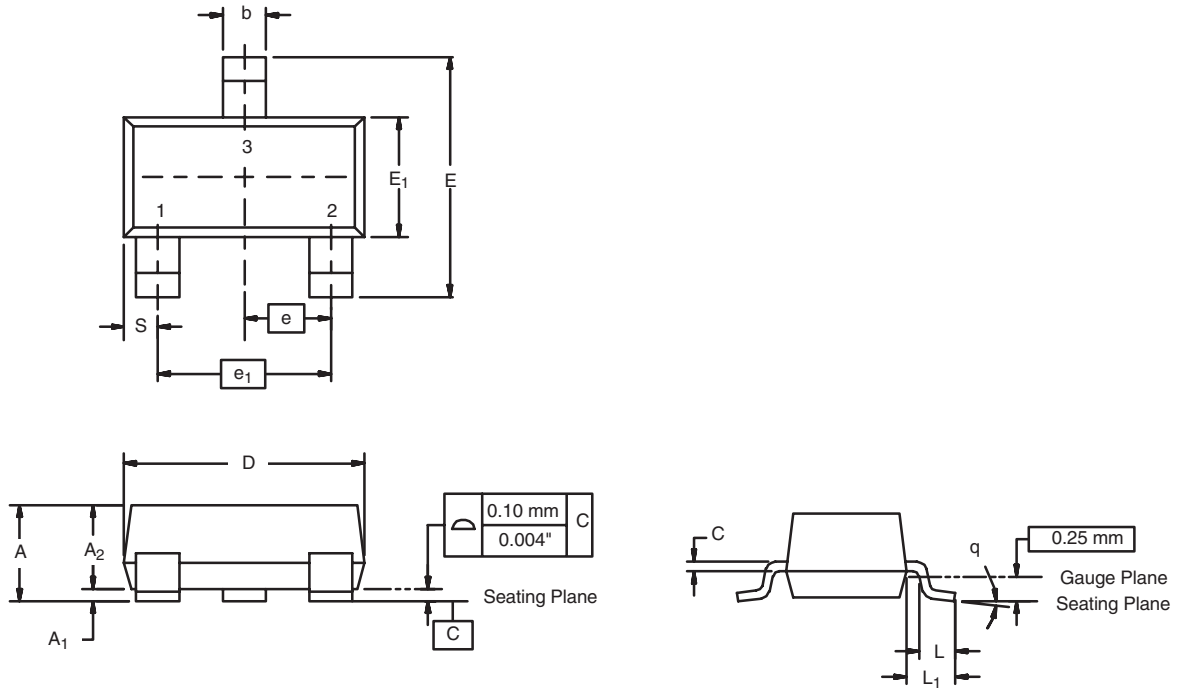


Single Pulse Power



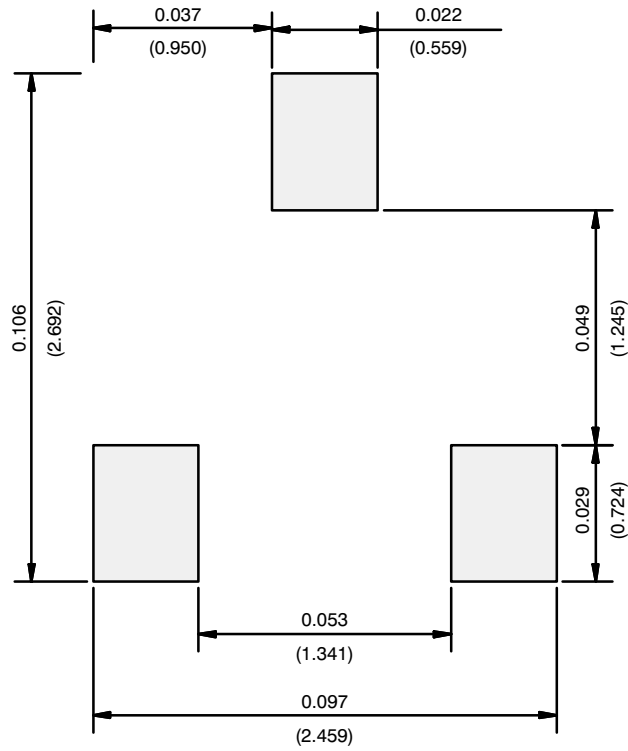
Normalized Thermal Transient Impedance, Junction-to-Ambient

SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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